

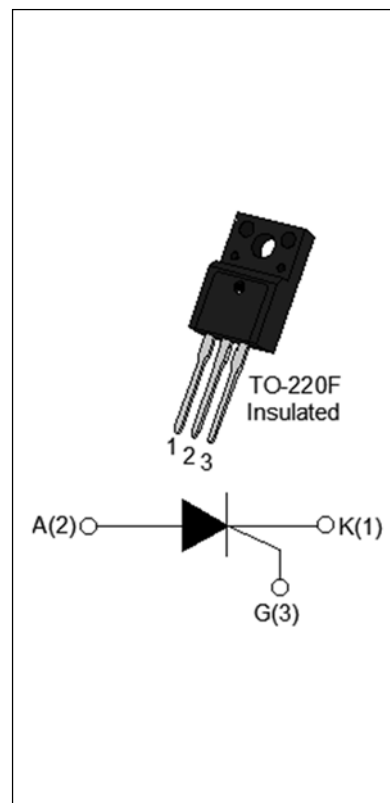


DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1230F SCR provide high dv/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT1230F provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	30	A
V_{DRM}/V_{RRM}	1200	V
I_{GT}	≤ 40	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range	T_j	-40-125	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	1200	V
Average on-state current ($T_c \leq 46^{\circ}C$)	$I_{T(AV)}$	19	A
RMS on-state current ($T_c \leq 46^{\circ}C$)	$I_{T(RMS)}$	30	A
Non repetitive surge peak on-state current ($t_p=10ms$, $T_j=25^{\circ}C$)	I_{TSM}	370	A
Non repetitive surge peak on-state current ($t_p=8.3ms$, $T_j=25^{\circ}C$)		400	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	685	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^{\circ}C$)	di/dt	200	$A/\mu s$

Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	10	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	-	-	40	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ C$ $R_L=3.3k\Omega$	0.25	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	120	mA
I_H	$I_T=1A$	-	-	100	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125^\circ C$	1500	-	-	V/ μs
t_{on}	$I_G=100mA$ $I_A=1A$ $I_R=100mA$ $T_j=25^\circ C$	-	5	-	μs
t_{off}		-	70	-	

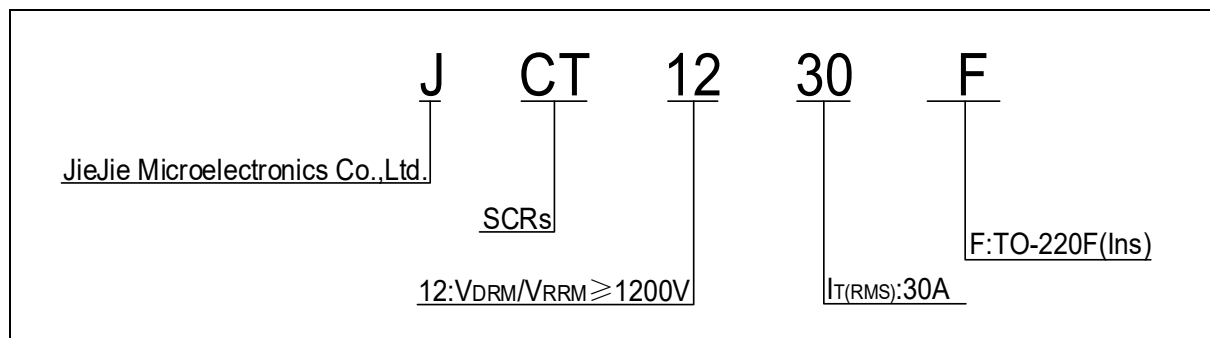
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=60A$ $t_p=380\mu s$	$T_j=25^\circ C$	1.55	V
V_{TO}	Threshold voltage	$T_j=125^\circ C$	0.76	V
R_D	Dynamic resistance	$T_j=125^\circ C$	15	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	8	μA
I_{RRM}		$T_j=125^\circ C$	3	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	2.1	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (DC)	60	$^\circ C/W$

ORDERING INFORMATION



MARKING

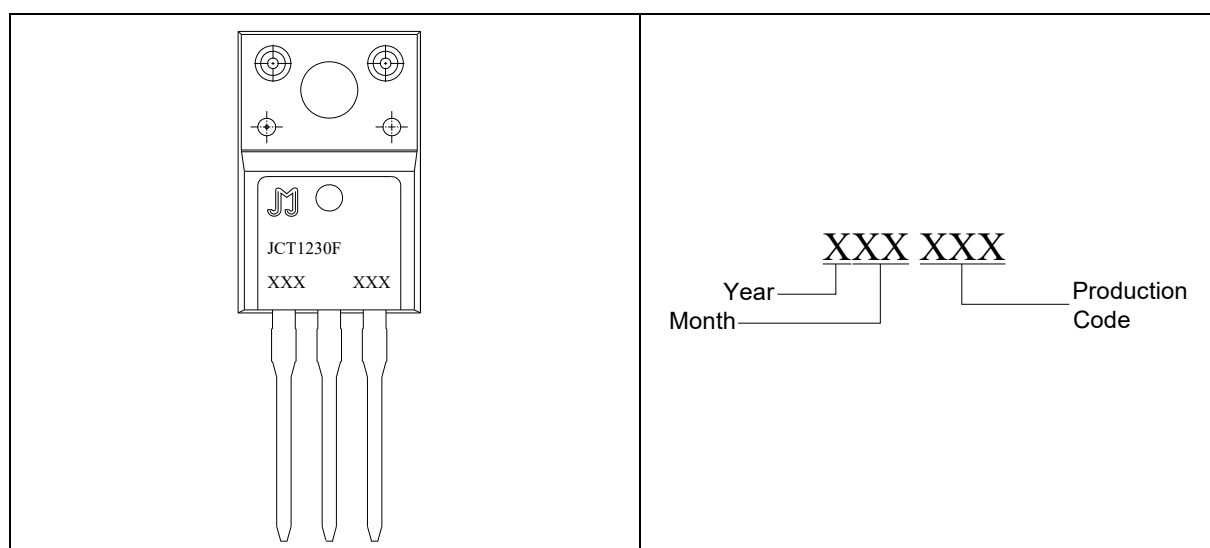


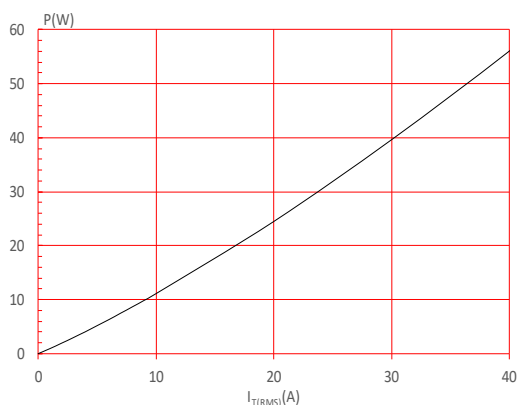
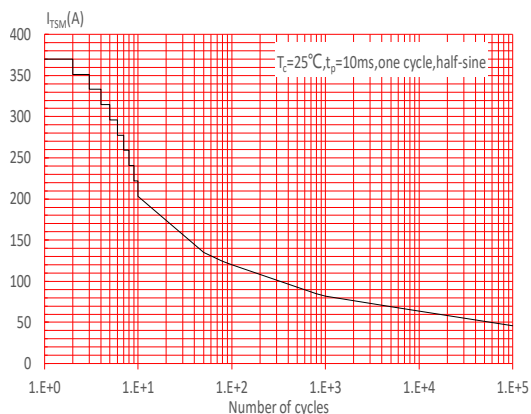
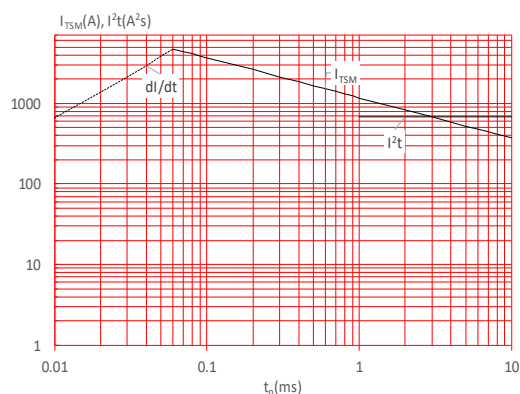
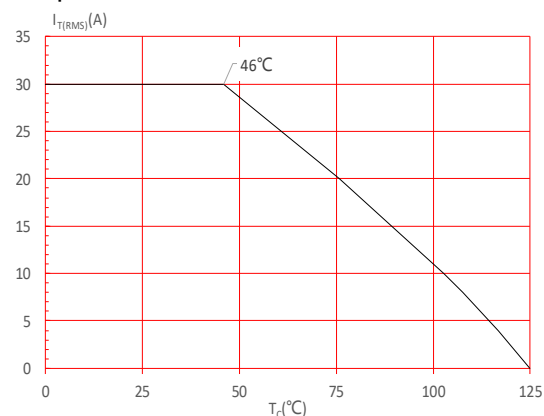
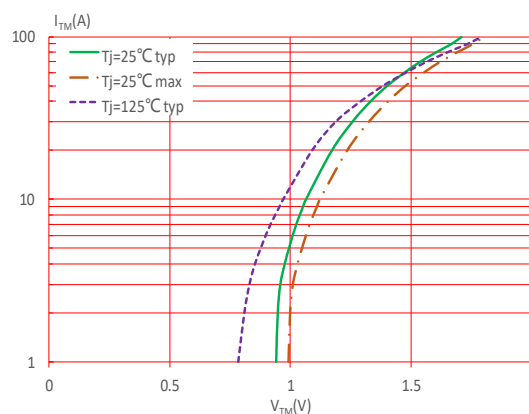
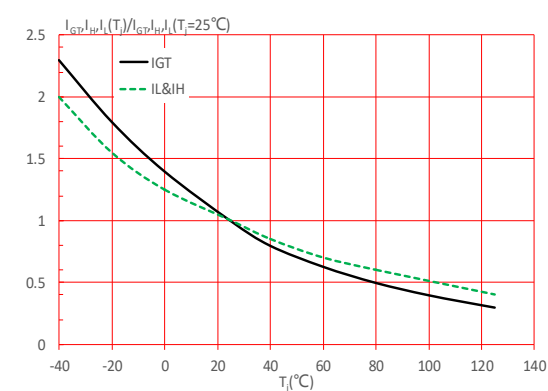
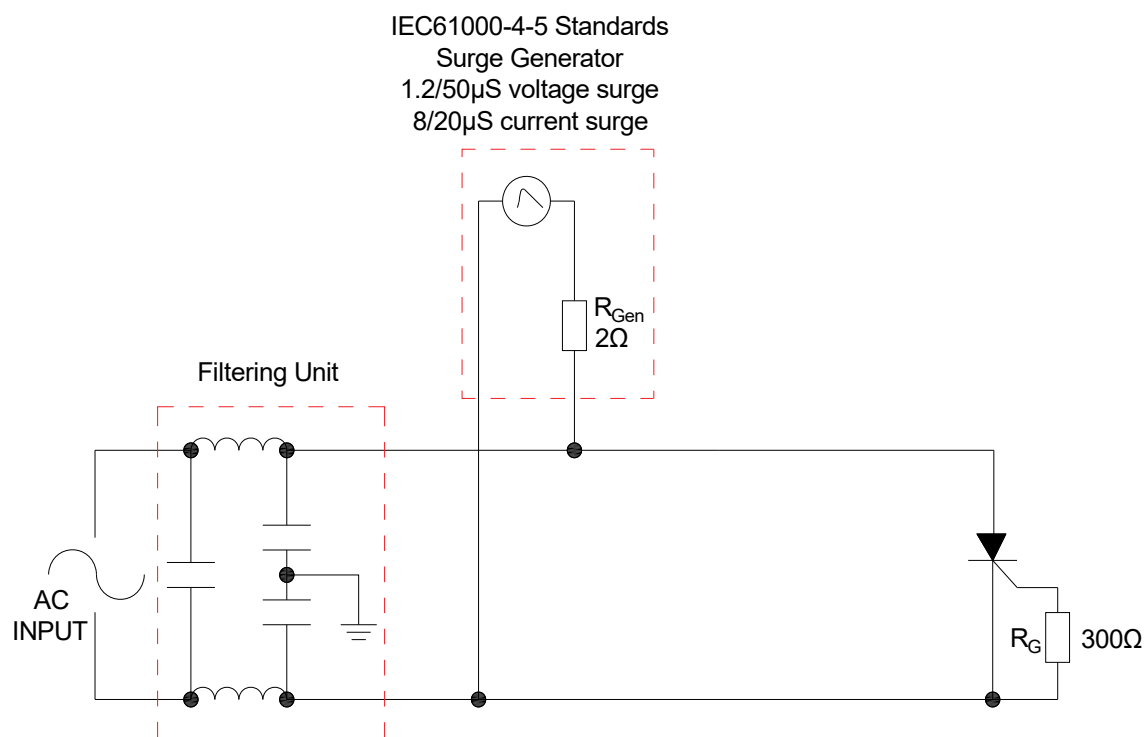
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.3: Surge peak on-state current versus number of cycles

FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$, and corresponding value of I^2t ($di/dt < 200A/\mu s$)

FIG.2: RMS on-state current versus case temperature

FIG.4: On-state characteristics

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics.

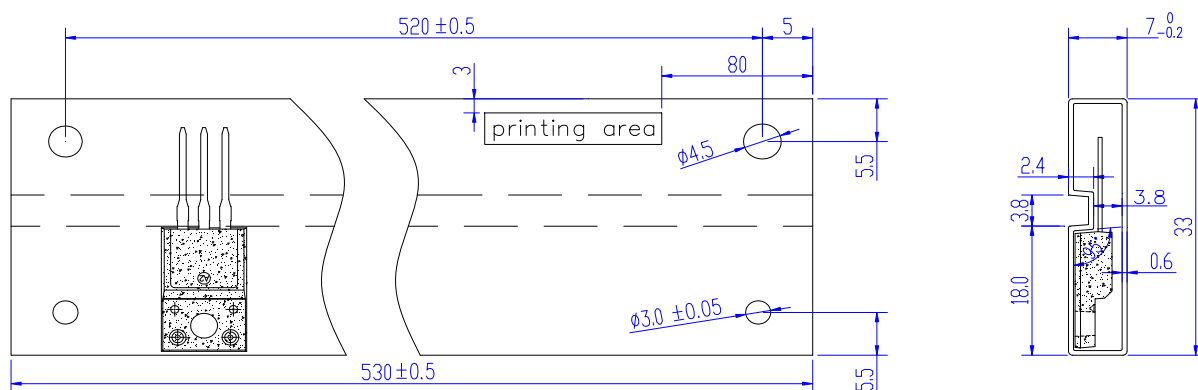
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1230F	1200	40	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Sept.29, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000

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